CEPF630B/CEBF630B
CEIF630B/CEFF630B

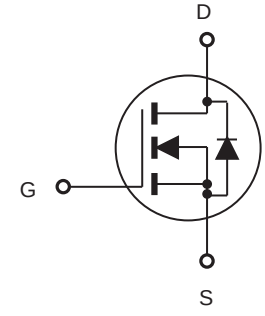
N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

FEATURES

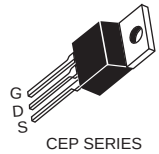
Type	V_{DSS}	$R_{DS(ON)}$	I_D	@V_{GS}
CEPF630B	200V	0.4Ω	9A	10V
CEBF630B	200V	0.4Ω	9A	10V
CEIF630B	200V	0.4Ω	9A	10V
CEFF630B	200V	0.4Ω	9A [e]	10V

- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- Lead free product is acquired.
- TO-220 & TO-263 & TO-262 package & TO-220F full-pak for through hole.

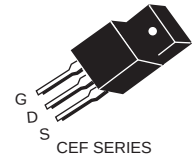


CEB SERIES
TO-263(DD-PAK)

CEI SERIES
TO-262(I2-PAK)



CEP SERIES
TO-220



CEF SERIES
TO-220F

ABSOLUTE MAXIMUM RATINGS T_C = 25°C unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263/262	TO-220F	
Drain-Source Voltage	V_{DS}	200		V
Gate-Source Voltage	V_{GS}	±30		V
Drain Current-Continuous	I_D	9	9 [e]	A
Drain Current-Pulsed [a]	I_{DM} [f]	36	36 [e]	A
Maximum Power Dissipation @ T_C = 25°C	P_D	74	35	W
- Derate above 25°C		0.59	0.28	W/°C
Single Pulsed Avalanche Energy [d]	E_{AS}	150	150	mJ
Single Pulsed Avalanche Current [d]	I_{AS}	9	9	A
Operating and Store Temperature Range	T_J,T_{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.7	3.6	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	65	°C/W

查询"CEFF630B"供应商

CEPF630B/CEBF630B
CEIF630B/CEFF630B

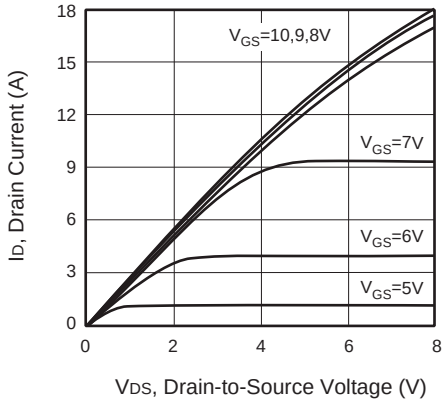


Figure 1. Output Characteristics

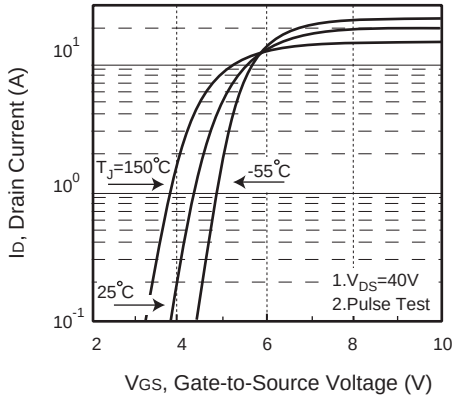


Figure 2. Transfer Characteristics

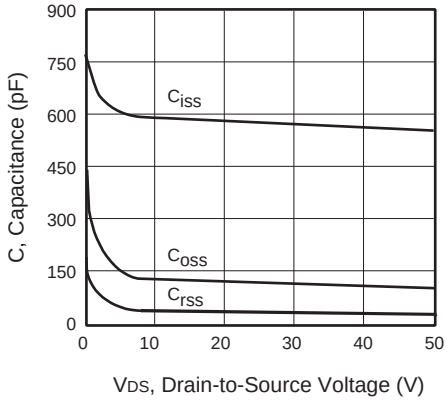


Figure 3. Capacitance

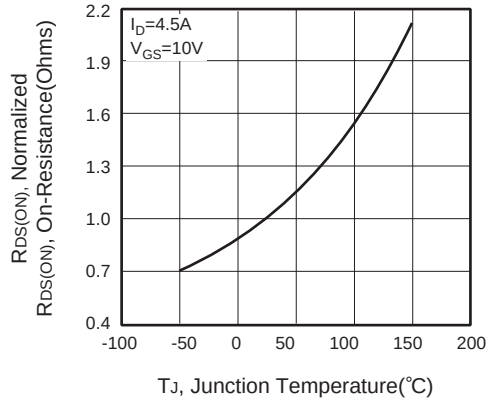


Figure 4. On-Resistance Variation with Temperature

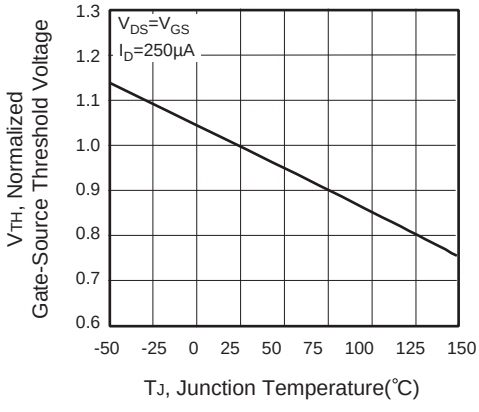


Figure 5. Gate Threshold Variation with Temperature

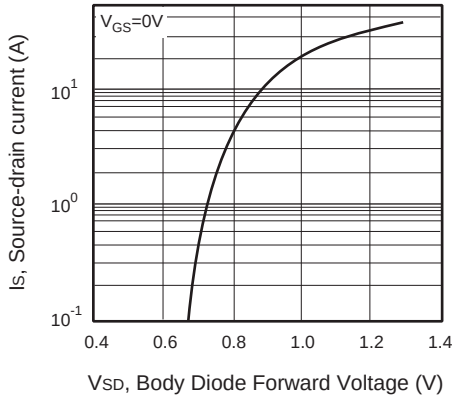


Figure 6. Body Diode Forward Voltage Variation with Source Current

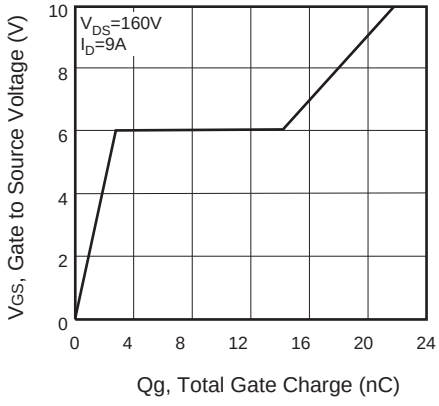


Figure 7. Gate Charge

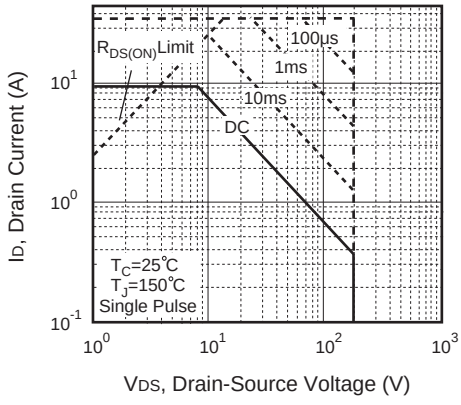


Figure 8. Maximum Safe Operating Area

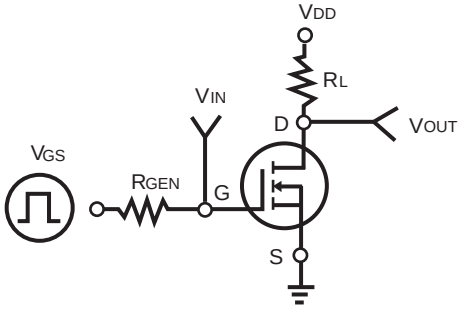


Figure 9. Switching Test Circuit

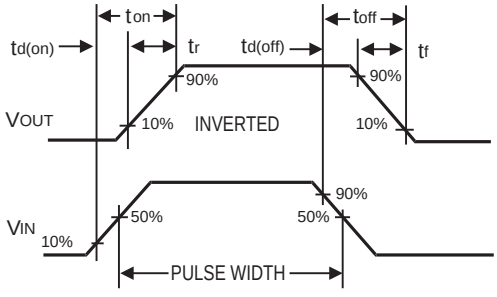


Figure 10. Switching Waveforms

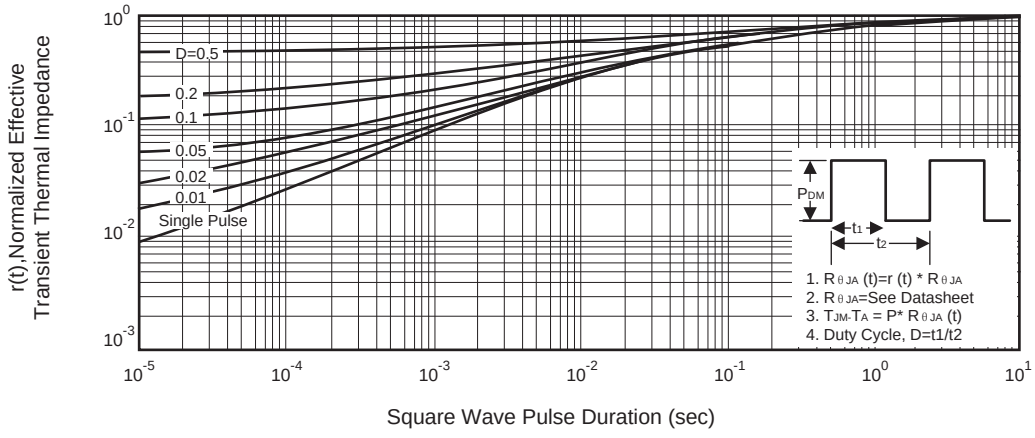


Figure 11. Normalized Thermal Transient Impedance Curve